2N4351

CASE 20-03, STYLE 2
TO-72 (TO-206AF)

MOS FET
SWITCHING

N-CHANNEL — ENHANCEMENT

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	25	Vdc
Drain-Gate Voltage	V_{DG}	30	Vdc
Gate-Source Voltage*	V_{GS}	30	Vdc
Drain Current	I_D	30	mAdc
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	300 1.7	mW mW/°C
Total Device Dissipation @ T_C = 25°C Derate above 25°C	P_D	800 4.56	mW mW/°C
Junction Temperature Range	T_J	175	°C
Storage Temperature Range	T_{stg}	−65 to +175	°C

*Transient potentials of ±75 Volt will not cause gate-oxide failure.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Drain-Source Breakdown Voltage (I_D = 10 μA, V_{GS} = 0)	$V_{(BR)DSX}$	25	—	Vdc
Zero-Gate-Voltage Drain Current (V_{DS} = 10 V, V_{GS} = 0) T_A = 25°C T_A = 150°C	I_{DSS}	— —	10 10	nAdc μAdc
Gate Reverse Current (V_{GS} = ±15 Vdc, V_{DS} = 0)	I_{GSS}	—	±10	pAdc
ON CHARACTERISTICS				
Gate Threshold Voltage (V_{DS} = 10 V, I_D = 10 μA)	$V_{GS(Th)}$	1.0	5	Vdc
Drain-Source On-Voltage (I_D = 2.0 mA, V_{GS} = 10 V)	$V_{DS(on)}$	—	1.0	V
On-State Drain Current (V_{GS} = 10 V, V_{DS} = 10 V)	$I_{D(on)}$	3.0	—	mAdc
SMALL-SIGNAL CHARACTERISTICS				
Forward Transfer Admittance (V_{DS} = 10 V, I_D = 2.0 mA, f = 1.0 kHz)	$\|Y_{fs}\|$	1000	—	μmho
Input Capacitance (V_{DS} = 10 V, V_{GS} = 0, f = 140 kHz)	C_{iss}	—	5.0	pF
Reverse Transfer Capacitance (V_{DS} = 0, V_{GS} = 0, f = 140 kHz)	C_{rss}	—	1.3	pF
Drain-Substrate Capacitance ($V_{D(SUB)}$ = 10 V, f = 140 kHz)	$C_{d(sub)}$	—	5.0	pF
Drain-Source Resistance (V_{GS} = 10 V, I_D = 0, f = 1.0 kHz)	$r_{ds(on)}$	—	300	ohms
SWITCHING CHARACTERISTICS				
Turn-On Delay (Fig. 5)	t_{d1}	—	45	ns
Rise Time (Fig. 6)	t_r	—	65	ns
Turn-Off Delay (Fig. 7)	t_{d2}	—	60	ns
Fall Time (Fig. 8)	t_f	—	100	ns

(I_D = 2.0 mAdc, V_{DS} = 10 Vdc, V_{GS} = 10 Vdc) (See Figure 9; Times Circuit Determined)

FIGURE 1 — FORWARD TRANSFER ADMITTANCE

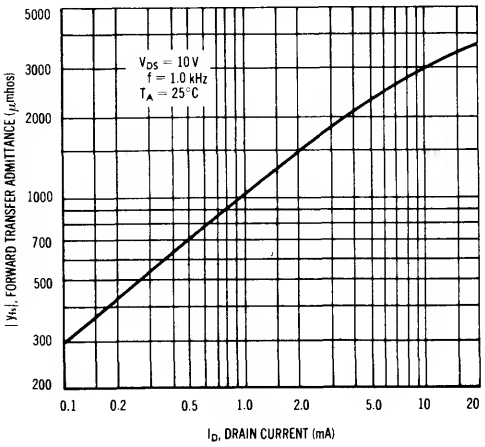


FIGURE 2 — TRANSFER CHARACTERISTICS

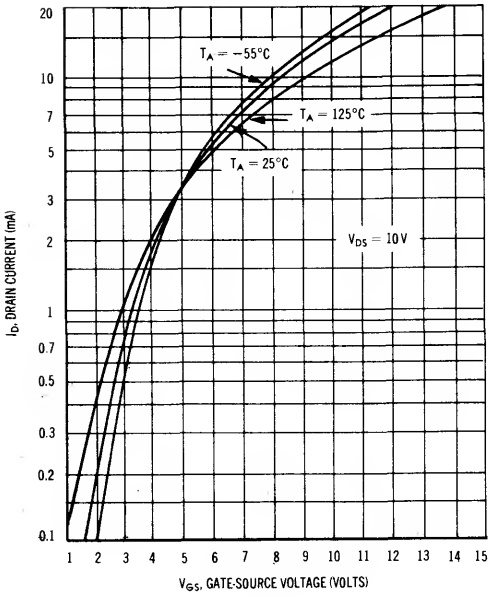


FIGURE 3 — DRAIN-SOURCE "ON" RESISTANCE

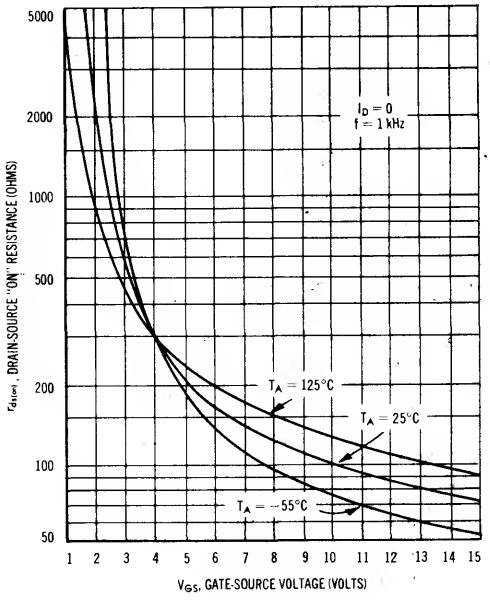
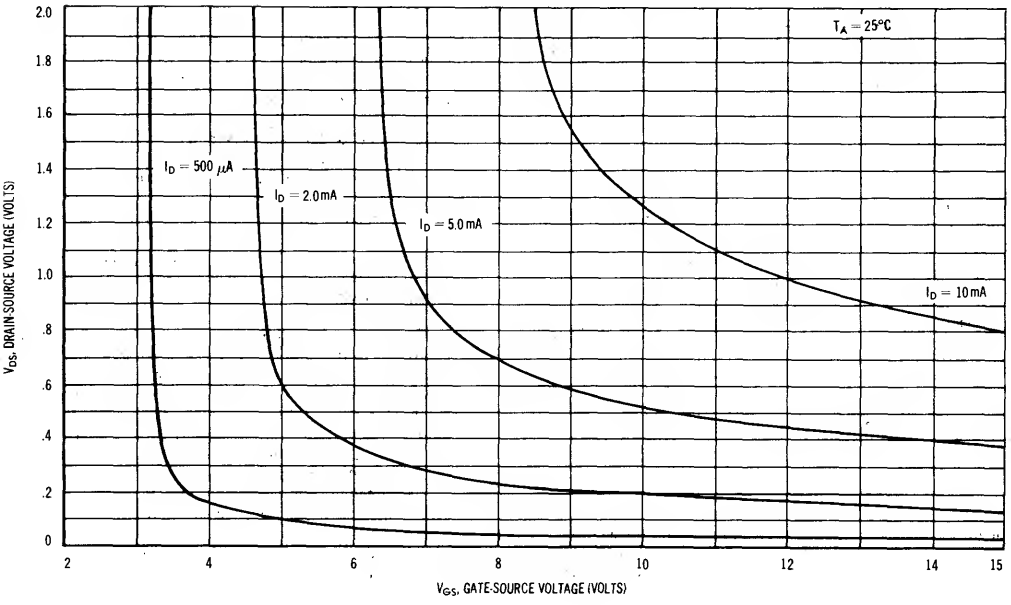


FIGURE 4 — "ON" DRAIN-SOURCE VOLTAGE



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SWITCHING CHARACTERISTICS
($T_A = 25°C$)

FIGURE 5 — TURN-ON DELAY TIME

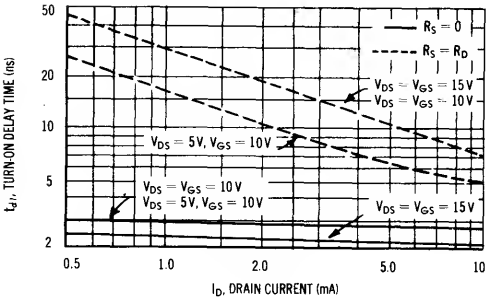


FIGURE 6 — RISE TIME

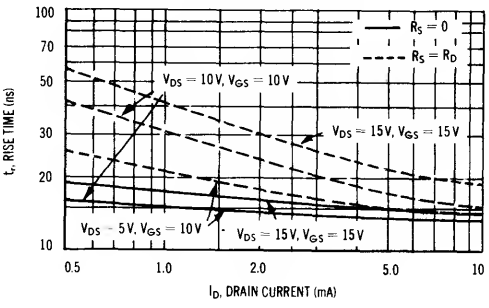


FIGURE 7 — TURN-OFF DELAY TIME

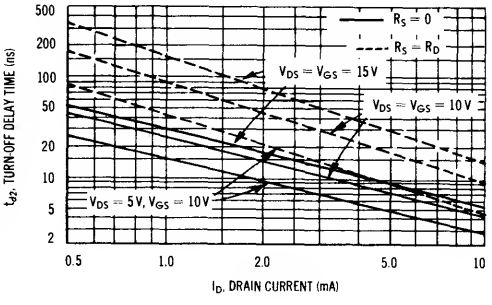


FIGURE 8 — FALL TIME

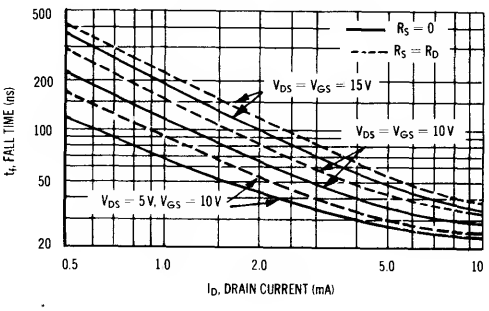
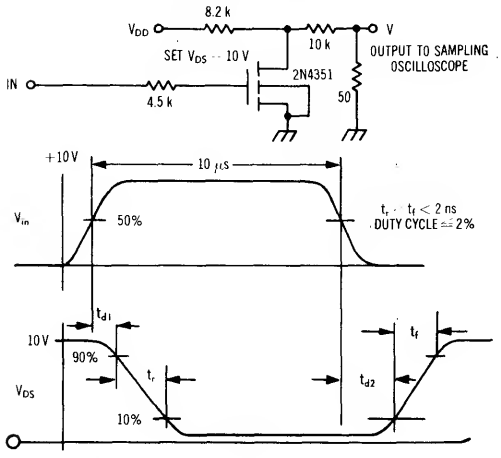


FIGURE 9 — SWITCHING CIRCUIT and WAVEFORMS



The switching characteristics shown above were measured in a test circuit similar to Figure 10. At the beginning of the switching interval, the gate voltage is at ground and the gate-source capacitance ($C_{gs} = C_{iss} - C_{rss}$) has no charge. The drain voltage is at V_{DD}, and thus the feedback capacitance (C_{rss}) is charged to V_{DD}. Similarly, the drain-substrate capacitance ($C_{d(sub)}$) is charged to V_{DD} since the substrate and source are connected to ground.

During the turn-on interval, C_{gs} is charged to V_{GS} (the input voltage) through R_S (generator impedance). C_{rss} must be discharged to $V_{GS} - V_{D(on)}$ through R_S and the parallel combination of the load resistor (R_D) and the channel resistance (r_{ds}). In addition, $C_{d(sub)}$ is discharged to a low value ($V_{D(on)}$) through R_D in parallel with r_{ds}. During turn-off this charge flow is reversed.

Predicting turn-on time proves to be somewhat difficult since the channel resistance (r_{ds}) is a function of the gate-source voltage (V_{GS}). As C_{gs} becomes charged, V_{GS} is approaching V_{in} and r_{ds} decreases (see Figure 4) and since C_{rss} and $C_{d(sub)}$ are charged through r_{ds}, turn-on time is quite non-linear.

If the charging time of C_{gs} is short compared to that of C_{rss} and $C_{d(sub)}$, then r_{ds} (which is in parallel with R_D) will be low compared to R_D during the switching interval and will largely determine the turn-on time. On the other hand, during turn-off r_{ds} will be almost an open circuit requiring C_{rss} and $C_{d(sub)}$ to be charged through R_D and resulting in a turn-off time that is long compared to the turn-on time. This is especially noticeable for the curves where $R_S = 0$ and C_{gs} is charged through the pulse generator impedance only.

The switching curves shown with $R_S = R_D$ simulate the switching behavior of cascaded stages where the driving source impedance is normally the same as the load impedance. The set of curves with $R_S = 0$ simulates a low source impedance drive such as might occur in complementary logic circuits.

FIGURE 10 — SWITCHING CIRCUIT MOSFET EQUIVALENT MODEL